MOTOROLA
SEMICONDUCTORS
3501 ED BLUESTEIN BLVD., AUSTIN, TEXAS 78721

MC6850

MOS
(N-CHANNEL, SILICON-GATE)

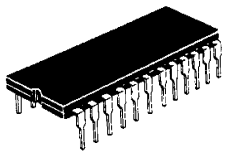
ASYNCHRONOUS COMMUNICATIONS INTERFACE ADAPTER

ASYNCHRONOUS COMMUNICATIONS INTERFACE ADAPTER (ACIA)

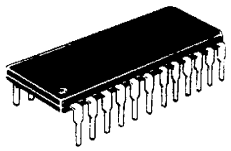
The MC6850 Asynchronous Communications Interface Adapter provides the data formatting and control to interface serial asynchronous data communications information to bus organized systems such as the MC6800 Microprocessing Unit.

The bus interface of the MC6850 includes select, enable, read/write, interrupt and bus interface logic to allow data transfer over an 8-bit bidirectional data bus. The parallel data of the bus system is serially transmitted and received by the asynchronous data interface, with proper formatting and error checking. The functional configuration of the ACIA is programmed via the data bus during system initialization. A programmable Control Register provides variable word lengths, clock division ratios, transmit control, receive control, and interrupt control. For peripheral or modem operation, three control lines are provided. These lines allow the ACIA to interface directly with the MC6860L 0-600 bps digital modem.

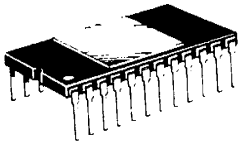
- 8- and 9-Bit Transmission
- Optional Even and Odd Parity
- Parity, Overrun and Framing Error Checking
- Programmable Control Register
- Optional ÷1, ÷16, and ÷64 Clock Modes
- Up to 1.0 Mbps Transmission
- False Start Bit Deletion
- Peripheral/Modem Control Functions
- Double Buffered
- One- or Two-Stop Bit Operation



S SUFFIX
CERDIP PACKAGE
CASE 623

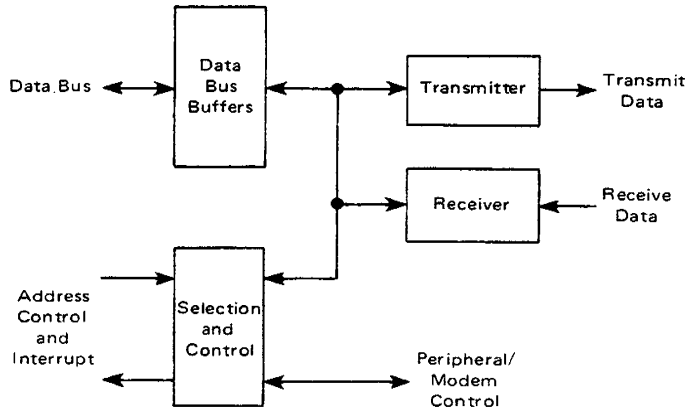


P SUFFIX
PLASTIC PACKAGE
CASE 709

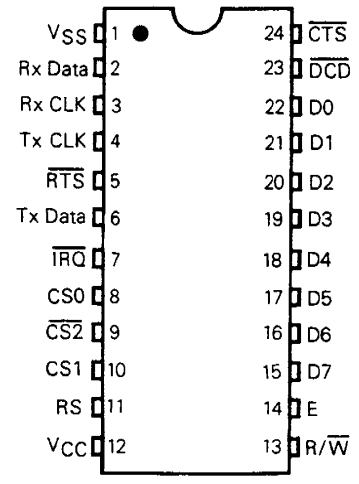


L SUFFIX
CERAMIC PACKAGE
CASE 716

MC6850 ASYNCHRONOUS COMMUNICATIONS INTERFACE ADAPTER BLOCK DIAGRAM



PIN ASSIGNMENT



MAXIMUM RATINGS

Characteristics	Symbol	Value	Unit
Supply Voltage	V_{CC}	−0.3 to +7.0	V
Input Voltage	V_{in}	−0.3 to +7.0	V
Operating Temperature Range MC6850, MC68A50, MC68B50 MC6850C, MC68A50C	T_A	T_L to T_H 0 to 70 −40 to +85	°C
Storage Temperature Range	T_{stg}	−55 to +150	°C

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{CC}).

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance Plastic Ceramic Cerdip	θ_{JA}	 120 60 65	°C/W

POWER CONSIDERATIONS

The average chip-junction temperature, T_J, in °C can be obtained from:

$$T_J = T_A + (P_D \bullet \theta_{JA}) \quad (1)$$

Where:

$T_A \equiv$ Ambient Temperature, °C

$\theta_{JA} \equiv$ Package Thermal Resistance, Junction-to-Ambient, °C/W

$P_D \equiv P_{INT} + P_{PORT}$

$P_{INT} \equiv I_{CC} \times V_{CC}$, Watts — Chip Internal Power

$P_{PORT} \equiv$ Port Power Dissipation, Watts — User Determined

For most applications $P_{PORT} \ll P_{INT}$ and can be neglected. P_{PORT} may become significant if the device is configured to drive Darlington bases or sink LED loads.

An approximate relationship between P_D and T_J (if P_{PORT} is neglected) is:

$$P_D = K \div (T_J + 273°C) \quad (2)$$

Solving equations (1) and (2) for K gives:

$$K = P_D \bullet (T_A + 273°C) + \theta_{JA} \bullet P_D 2 \quad (3)$$

Where K is a constant pertaining to the particular part. K can be determined from equation (3) by measuring P_D (at equilibrium) for a known T_A. Using this value of K, the values of P_D and T_J can be obtained by solving equations (1) and (2) iteratively for any value of T_A.

DC ELECTRICAL CHARACTERISTICS (V_{CC} = 5.0 Vdc ±5%, V_{SS} = 0, $T_A = T_L$ to T_H unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
Input High Voltage		V_{IH}	V_{SS}+2.0	–	V_{CC}	V
Input Low Voltage		V_{IL}	V_{SS}−0.3	–	V_{SS}+0.8	V
Input Leakage Current (V_{in} = 0 to 5.25 V)	R/$\overline{W}$, CS0, CS1, $\overline{CS2}$, Enable RS, Rx D, Rx C, $\overline{CTS}$, $\overline{DCD}$	I_{in}	–	1.0	2.5	μA
Hi-Z (Off State) Input Current (V_{in} = 0.4 to 2.4 V)	D0-D7	I_{TSI}	–	2.0	10	μA
Output High Voltage (I_{Load} = −205 μA, Enable Pulse Width < 25 μs) (I_{Load} = −100 μA, Enable Pulse Width < 25 μs)	D0-D7 Tx Data, $\overline{RTS}$	V_{OH}	V_{SS}+2.4 V_{SS}+2.4	– –	– –	V
Output Low Voltage (I_{Load} = 1.6 mA, Enable Pulse Width < 25 μs)		V_{OL}	–	–	V_{SS}+0.4	V
Output Leakage Current (Off State) (V_{OH} = 2.4 V)	$\overline{IRQ}$	I_{LOH}	–	1.0	10	μA
Internal Power Dissipation (Measured at T_A = 0°C)		P_{INT}	–	300	525*	mW
Internal Input Capacitance (V_{in} = 0, T_A = 25°C, f = 1.0 MHz) E, Tx CLK, Rx CLK, R/$\overline{W}$, RS, Rx Data, CS0, CS1, $\overline{CS2}$, $\overline{CTS}$, $\overline{DCD}$	D0-D7	C_{in}	– –	10 7.0	12.5 7.5	pF
Output Capacitance (V_{in} = 0, T_A = 25°C, f = 1.0 MHz)	RTS, Tx Data $\overline{IRQ}$	C_{out}	– –	– –	10 5.0	pF

*For temperatures less than T_A = 0°C, P_{INT} maximum will increase.

SERIAL DATA TIMING CHARACTERISTICS

Characteristic		Symbol	MC6850		MC68A50		MC68B50		Unit
			Min	Max	Min	Max	Min	Max	
Data Clock Pulse Width, Low (See Figure 1)	÷16, ÷64 Modes	PW_{CL}	600	–	450	–	280	–	ns
	÷1 Mode		900	–	650	–	500	–	
Data Clock Pulse Width, High (See Figure 2)	÷16, ÷64 Modes	PW_{CH}	600	–	450	–	280	–	ns
	÷1 Mode		900	–	650	–	500	–	
Data Clock Frequency	÷16, ÷64 Modes	f_C	–	0.8	–	1.0	–	1.5	MHz
	÷1 Mode		–	500	–	750	–	1000	kHz
Data Clock-to-Data Delay for Transmitter (See Figure 3)		t_{TDD}	–	600	–	540	–	460	ns
Receive Data Setup Time (See Figure 4)	÷1 Mode	t_{RDS}	250	–	100	–	30	–	ns
Receive Data Hold Time (See Figure 5)	÷1 Mode	t_{RDH}	250	–	100	–	30	–	ns
Interrupt Request Release Time (See Figure 6)		t_{IR}	–	1.2	–	0.9	–	0.7	μs
Request-to-Send Delay Time (See Figure 6)		t_{RTS}	–	560	–	480	–	400	ns
Input Rise and Fall Times (or 10% of the pulse width if smaller)		t_r, t_f	–	1.0	–	0.5	–	0.25	μs

FIGURE 1 — CLOCK PULSE WIDTH, LOW-STATE

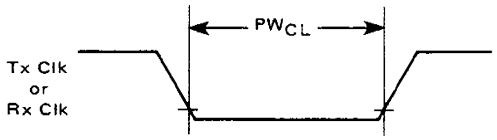


FIGURE 2 — CLOCK PULSE WIDTH, HIGH-STATE

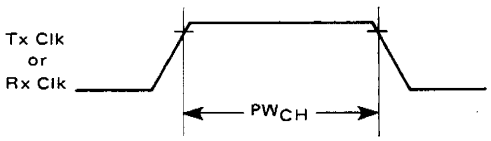


FIGURE 3 — TRANSMIT DATA OUTPUT DELAY

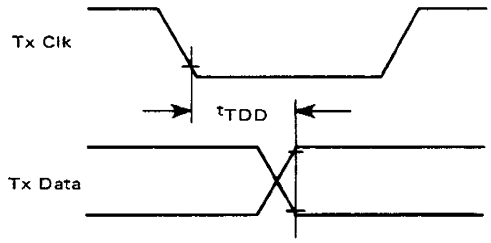


FIGURE 4 — RECEIVE DATA SETUP TIME (÷1 Mode)

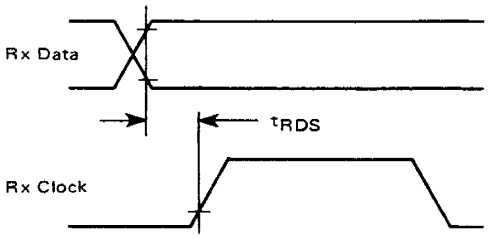


FIGURE 5 — RECEIVE DATA HOLD TIME (÷1 Mode)

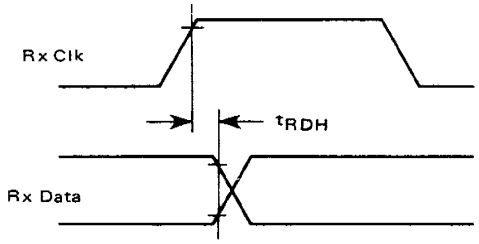
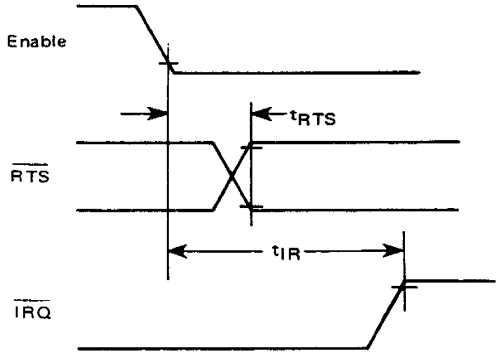


FIGURE 6 — REQUEST-TO-SEND DELAY AND INTERRUPT-REQUEST RELEASE TIMES



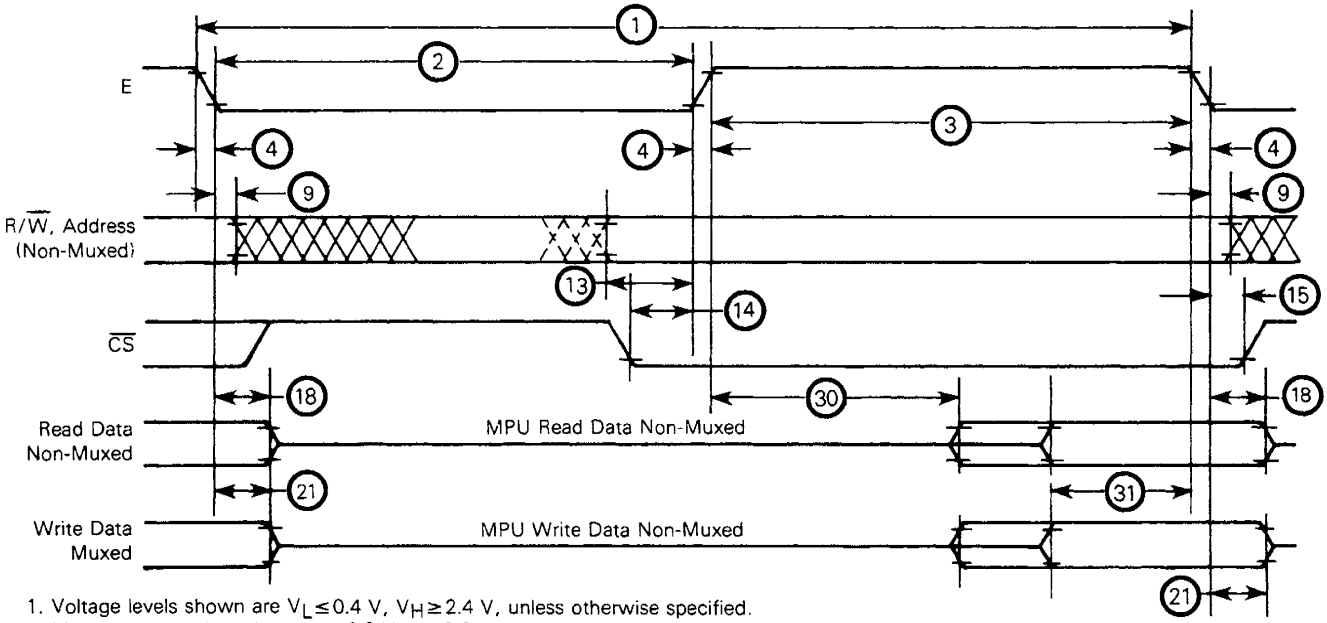
Note: Timing measurements are referenced to and from a low voltage of 0.8 volts and a high voltage of 2.0 volts, unless otherwise noted.

BUS TIMING CHARACTERISTICS (See Notes 1 and 2 and Figure 7)

Ident. Number	Characteristic	Symbol	MC6850		MC68A50		MC68B50		Unit
			Min	Max	Min	Max	Min	Max	
1	Cycle Time	t_{cyc}	1.0	10	0.67	10	0.5	10	μs
2	Pulse Width, E Low	PW_{EL}	430	9500	280	9500	210	9500	ns
3	Pulse Width, E High	PW_{EH}	450	9500	280	9500	220	9500	ns
4	Clock Rise and Fall Time	t_r, t_f	–	25	–	25	–	20	ns
9	Address Hold Time	t_{AH}	10	–	10	–	10	–	ns
13	Address Setup Time Before E	t_{AS}	80	–	60	–	40	–	ns
14	Chip Select Setup Time Before E	t_{CS}	80	–	60	–	40	–	ns
15	Chip Select Hold Time	t_{CH}	10	–	10	–	10	–	ns
18	Read Data Hold Time	t_{DHR}	20	50*	20	50*	20	50*	ns
21	Write Data Hold Time	t_{DHW}	10	–	10	–	10	–	ns
30	Output Data Delay Time	t_{DDR}	–	290	–	180	–	150	ns
31	Input Data Setup Time	t_{DSW}	165	–	80	–	60	–	ns

*The data bus output buffers are no longer sourcing or sinking current by t_{DHR}max (High Impedance).

FIGURE 7 — BUS TIMING CHARACTERISTICS



1. Voltage levels shown are $V_L \leq 0.4$ V, $V_H \geq 2.4$ V, unless otherwise specified.
2. Measurement points shown are 0.8 V and 2.0 V, unless otherwise specified.

FIGURE 8 — BUS TIMING TEST LOADS